**AMMPLEON** 

Product data sheet

#### **Product profile** 1.

### 1.1 General description

A 1200 W LDMOS power transistor for broadcast applications and industrial applications in the HF to 500 MHz band.

Table 1. **Application information** 

| Mode of operation | f     | V <sub>DS</sub> | $P_L$ | G <sub>p</sub> | $\eta_D$ |
|-------------------|-------|-----------------|-------|----------------|----------|
|                   | (MHz) | (V)             | (W)   | (dB)           | (%)      |
| CW                | 108   | 50              | 1000  | 26             | 75       |
| pulsed RF         | 225   | 50              | 1200  | 24             | 71       |

#### 1.2 Features and benefits

- Typical pulsed performance at frequency of 225 MHz, a supply voltage of 50 V and an  $I_{Da}$  of 40 mA, a  $t_p$  of 100  $\mu$ s with  $\delta$  of 20 %:
  - ◆ Output power = 1200 W
  - ◆ Power gain = 24 dB
  - ◆ Efficiency = 71 %
- Easy power control
- Integrated ESD protection
- Excellent ruggedness
- High efficiency
- Excellent thermal stability
- Designed for broadband operation (10 MHz to 500 MHz)
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)

### 1.3 Applications

- Industrial, scientific and medical applications
- Broadcast transmitter applications

**Power LDMOS transistor** 

# 2. Pinning information

Table 2. Pinning

| Pin | Description | Simplified outline | Graphic symbol |
|-----|-------------|--------------------|----------------|
| 1   | drain1      |                    | _              |
| 2   | drain2      | 1 2                | <u>ا</u>       |
| 3   | gate1       | <b>≥</b> 5 •       | 3—             |
| 4   | gate2       | 3 4                | 5              |
| 5   | source      | [1]                | 4 7            |
|     |             |                    | <b>'</b>       |
|     |             |                    | 2<br>sym117    |

[1] Connected to flange.

# 3. Ordering information

Table 3. Ordering information

| Type number | Package |                                                                       |         |
|-------------|---------|-----------------------------------------------------------------------|---------|
|             | Name    | Description                                                           | Version |
| BLF578      | -       | flanged balanced LDMOST ceramic package;<br>2 mounting holes; 4 leads | SOT539A |

# 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol           | Parameter            | Conditions | Min  | Max  | Unit |
|------------------|----------------------|------------|------|------|------|
| $V_{DS}$         | drain-source voltage |            | -    | 110  | V    |
| $V_{GS}$         | gate-source voltage  |            | -0.5 | +11  | V    |
| I <sub>D</sub>   | drain current        |            | -    | 88   | Α    |
| T <sub>stg</sub> | storage temperature  |            | -65  | +150 | °C   |
| Tj               | junction temperature |            | -    | 225  | °C   |

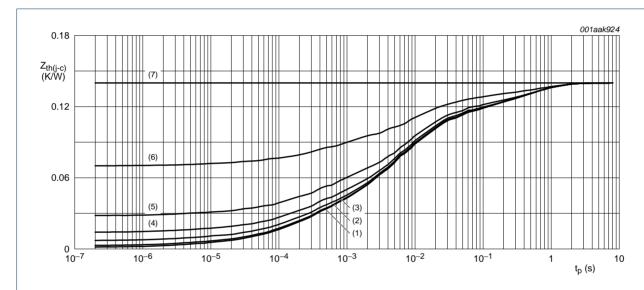
**Power LDMOS transistor** 

# 5. Thermal characteristics

Table 5. Thermal characteristics

| S | Symbol               | Parameter                                         | Conditions                                                           | Тур  | Unit |
|---|----------------------|---------------------------------------------------|----------------------------------------------------------------------|------|------|
| F | R <sub>th(j-c)</sub> | thermal resistance from junction to case          | $T_j = 150  ^{\circ}\text{C}$ [1][2]                                 | 0.14 | K/W  |
| Z | th(j-c)              | transient thermal impedance from junction to case | $T_j = 150 ^{\circ}\text{C}; t_p = 100 \mu\text{s};  \delta = 20 \%$ | 0.04 | K/W  |

- [1]  $T_i$  is the junction temperature.
- [2]  $R_{th(j-c)}$  is measured under RF conditions.
- [3] See Figure 1.



- (1)  $\delta = 1 \%$
- (2)  $\delta = 2 \%$
- (3)  $\delta = 5 \%$
- (4)  $\delta = 10 \%$
- (5)  $\delta = 20 \%$
- (6)  $\delta = 50 \%$
- (7)  $\delta = 100 \% (DC)$

Fig 1. Transient thermal impedance from junction to case as function of pulse duration

# 6. Characteristics

Table 6. DC characteristics

 $T_j$  = 25 °C; per section unless otherwise specified.

| Symbol              | Parameter                      | Conditions                                      | Min  | Тур | Max  | Unit |
|---------------------|--------------------------------|-------------------------------------------------|------|-----|------|------|
| $V_{(BR)DSS}$       | drain-source breakdown voltage | $V_{GS} = 0 \text{ V}; I_D = 2.5 \text{ mA}$    | 110  | -   | -    | V    |
| V <sub>GS(th)</sub> | gate-source threshold voltage  | V <sub>DS</sub> = 10 V; I <sub>D</sub> = 500 mA | 1.25 | 1.7 | 2.25 | V    |
| $V_{GSq}$           | gate-source quiescent voltage  | $V_{DS}$ = 50 V; $I_{D}$ = 20 mA                | 0.8  | 1.3 | 1.8  | V    |
| I <sub>DSS</sub>    | drain leakage current          | V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 50 V   | -    | -   | 2.8  | μА   |

### **Power LDMOS transistor**

Table 6. DC characteristics ...continued

 $T_i$  = 25 °C; per section unless otherwise specified.

| Symbol              | Parameter                        | Conditions                                                         | Min | Тур  | Max | Unit |
|---------------------|----------------------------------|--------------------------------------------------------------------|-----|------|-----|------|
| I <sub>DSX</sub>    | drain cut-off current            | $V_{GS} = V_{GS(th)} + 3.75 \text{ V};$<br>$V_{DS} = 10 \text{ V}$ | 58  | 70   | -   | A    |
| I <sub>GSS</sub>    | gate leakage current             | V <sub>GS</sub> = 11 V; V <sub>DS</sub> = 0 V                      | -   | -    | 280 | nA   |
| R <sub>DS(on)</sub> | drain-source on-state resistance | $V_{GS} = V_{GS(th)} + 3.75 \text{ V};$<br>$I_D = 16.66 \text{ A}$ | -   | 0.07 | -   | Ω    |
| C <sub>rs</sub>     | feedback capacitance             | $V_{GS} = 0 \text{ V}; V_{DS} = 50 \text{ V};$<br>f = 1 MHz        | -   | 3    | -   | pF   |
| C <sub>iss</sub>    | input capacitance                | V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 50 V;<br>f = 1 MHz        | -   | 403  | -   | pF   |
| Coss                | output capacitance               | V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 50 V;<br>f = 1 MHz        | -   | 138  | -   | pF   |

Table 7. RF characteristics

Mode of operation: pulsed RF;  $t_p$  = 100  $\mu$ s;  $\delta$  = 20 %; f = 225 MHz; RF performance at  $V_{DS}$  = 50 V;  $I_{Da}$  = 40 mA;  $T_{case}$  = 25 °C; unless otherwise specified; in a class-AB production test circuit.

| Symbol         | Parameter         | Conditions              | Min | Тур  | Max  | Unit |
|----------------|-------------------|-------------------------|-----|------|------|------|
| G <sub>p</sub> | power gain        | P <sub>L</sub> = 1200 W | 23  | 24   | 25.4 | dB   |
| RLin           | input return loss | P <sub>L</sub> = 1200 W | 14  | 17.5 | -    | dB   |
| $\eta_{D}$     | drain efficiency  | P <sub>L</sub> = 1200 W | 68  | 71   | -    | %    |

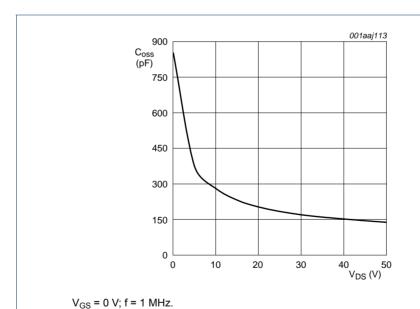


Fig 2. Output capacitance as a function of drain-source voltage; typical values per section

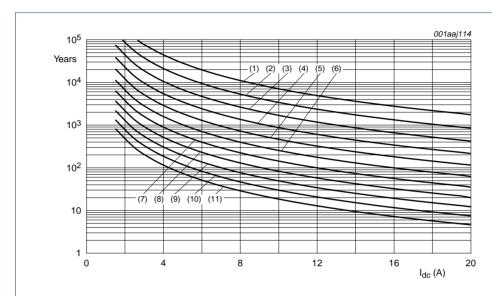
#### 6.1 Ruggedness in class-AB operation

The BLF578 is capable of withstanding a load mismatch corresponding to VSWR = 13 : 1 through all phases under the following conditions:  $V_{DS}$  = 50 V;  $I_{Dq}$  = 40 mA;  $P_{L}$  = 1200 W pulsed; f = 225 MHz.

**Power LDMOS transistor** 

# 7. Application information

# 7.1 Reliability



TTF (0.1 % failure fraction).

The reliability at pulsed conditions can be calculated as follows: TTF (0.1 %)  $\times$  1/  $\delta$ .

- (1)  $T_i = 100 \, ^{\circ}C$
- (2)  $T_j = 110 \, ^{\circ}C$
- (3)  $T_i = 120 \, ^{\circ}C$
- (4)  $T_i = 130 \, ^{\circ}C$
- (5)  $T_j = 140 \, ^{\circ}\text{C}$
- (6)  $T_j = 150 \, ^{\circ}C$
- (7)  $T_j = 160 \, ^{\circ}C$
- (8)  $T_i = 170 \, ^{\circ}\text{C}$
- (9)  $T_j = 180 \, ^{\circ}\text{C}$
- (10)  $T_j = 190 \, ^{\circ}C$
- (11)  $T_j = 200 \, ^{\circ}C$

Fig 3. BLF578 electromigration (I<sub>D</sub>, total device)

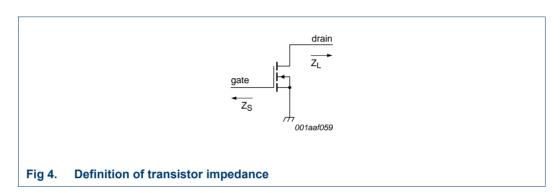
**Power LDMOS transistor** 

### 8. Test information

### 8.1 Impedance information

Table 8.Typical impedanceSimulated  $Z_S$  and  $Z_L$  test circuit impedances.

| f   | Zs         | Z <sub>L</sub> |
|-----|------------|----------------|
| MHz | Ω          | Ω              |
| 225 | 3.2 + j2.6 | 3.7 – j0.2     |



### 8.2 RF performance

The following figures are measured in a class-AB production test circuit.

### 8.2.1 1-Tone CW pulsed

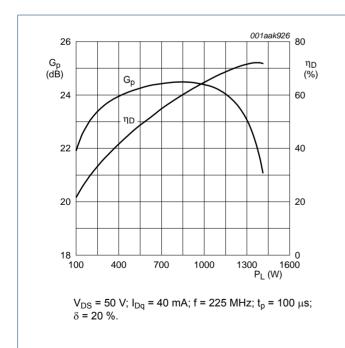
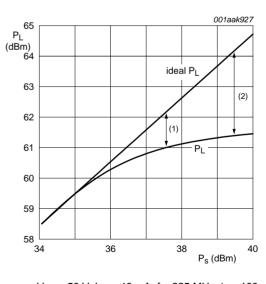


Fig 5. Power gain and drain efficiency as function of load power; typical values

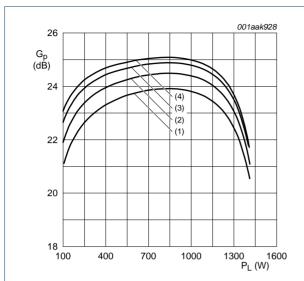


 $V_{DS}$  = 50 V;  $I_{Dq}$  = 40 mA; f = 225 MHz;  $t_p$  = 100  $\mu s$ ;  $\delta$  = 20 %.

- (1)  $P_{L(1dB)} = 61.0 \text{ dBm } (1260 \text{ W})$
- (2)  $P_{L(3dB)} = 61.4 \text{ dBm } (1400 \text{ W})$

Fig 6. Load Power as function of source power; typical values

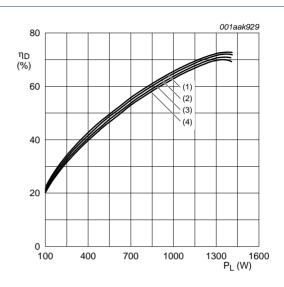
#### **Power LDMOS transistor**



 $V_{DS}$  = 50 V; f = 225 MHz;  $t_p$  = 100  $\mu$ s;  $\delta$  = 20 %.

- (1)  $I_{Dq} = 0 \text{ mA}$
- (2)  $I_{Dq} = 40 \text{ mA}$
- (3)  $I_{Dq} = 80 \text{ mA}$
- (4)  $I_{Dq} = 160 \text{ mA}$

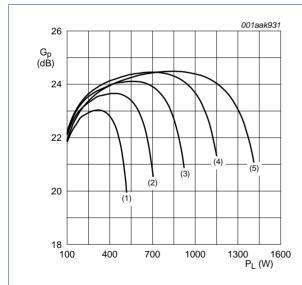
Fig 7. Power gain as a function of load power; typical values



 $V_{DS}$  = 50 V; f = 225 MHz;  $t_p$  = 100  $\mu$ s;  $\delta$  = 20 %.

- (1)  $I_{Dq} = 0 \text{ mA}$
- (2)  $I_{Dq} = 40 \text{ mA}$
- (3)  $I_{Dq} = 80 \text{ mA}$
- (4)  $I_{Dq} = 160 \text{ mA}$

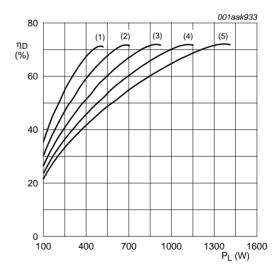
Fig 8. Drain efficiency as a function of load power; typical values



 $I_{Dq}$  = 40 mA; f = 225 MHz;  $t_p$  = 100  $\mu$ s;  $\delta$  = 20 %.

- (1)  $V_{DS} = 30 \text{ V}$
- (2)  $V_{DS} = 35 \text{ V}$
- (3)  $V_{DS} = 40 \text{ V}$
- (4)  $V_{DS} = 45 \text{ V}$
- (5)  $V_{DS} = 50 \text{ V}$

Fig 9. Power gain as a function of load power; typical values



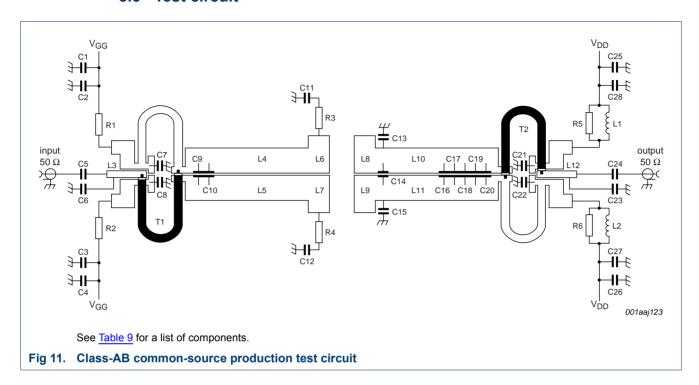
 $I_{Dq}$  = 40 mA; f = 225 MHz;  $t_p$  = 100  $\mu s;$   $\delta$  = 20 %.

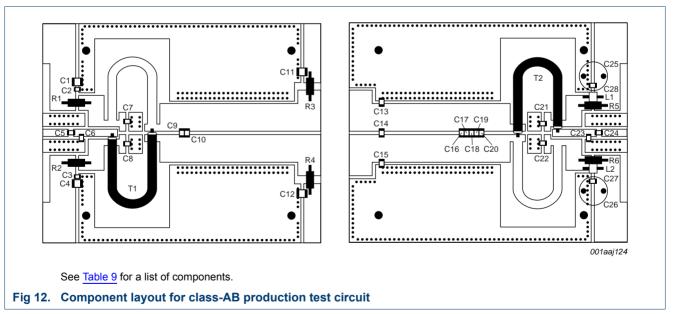
- (1)  $V_{DS} = 30 \text{ V}$
- (2)  $V_{DS} = 35 V$
- (3)  $V_{DS} = 40 \text{ V}$
- (4)  $V_{DS} = 45 V$
- (5)  $V_{DS} = 50 \text{ V}$

Fig 10. Drain efficiency as a function of load power; typical values

#### **Power LDMOS transistor**

### 8.3 Test circuit





#### **Power LDMOS transistor**

Table 9. List of components

For production test circuit, see Figure 11 and Figure 12.

Printed-Circuit Board (PCB): Rogers 5880;  $\varepsilon_r = 2.2 \text{ F/m}$ ; height = 0.79 mm; Cu (top/bottom metallization); thickness copper plating = 35  $\mu$ m.

| Component            | Description                       | Value                   | Remarks                |
|----------------------|-----------------------------------|-------------------------|------------------------|
| C1, C2, C11, C12     | multilayer ceramic chip capacitor | 4.7 μF                  | TDK4532X7R1E475Mt020U  |
| C2, C3, C27, C28     | multilayer ceramic chip capacitor | 100 nF                  | Murata X7R 250 V       |
| C5, C7, C8, C21, C22 | multilayer ceramic chip capacitor | 1 nF [1]                |                        |
| C6                   | multilayer ceramic chip capacitor | 30 pF [1]               |                        |
| C9, C10, C13, C15    | multilayer ceramic chip capacitor | 62 pF [1]               |                        |
| C14                  | multilayer ceramic chip capacitor | 36 pF [1]               |                        |
| C16, C17             | multilayer ceramic chip capacitor | 24 pF [1]               |                        |
| C18                  | multilayer ceramic chip capacitor | 30 pF [1]               |                        |
| C19                  | multilayer ceramic chip capacitor | 27 pF [1]               |                        |
| C20                  | multilayer ceramic chip capacitor | 9.1 pF <u>[1]</u>       |                        |
| C23                  | multilayer ceramic chip capacitor | 13 pF [1]               |                        |
| C24                  | multilayer ceramic chip capacitor | 16 pF [1]               |                        |
| C25, C26             | electrolytic capacitor            | 220 μF; 63 V            |                        |
| L1, L2               | 3 turns 1 mm copper wire          | D = 2 mm; length = 3 mm |                        |
| L3, L12              | stripline                         | -                       | (L × W) 15 mm × 2.4 mm |
| L4, L5, L10, L11     | stripline                         | -                       | (L × W) 47 mm × 10 mm  |
| L6, L7, L8, L9       | stripline                         | -                       | (L × W) 8 mm × 15 mm   |
| R1, R2               | metal film resistor               | 2 Ω; 0.6 W              |                        |
| R3, R4               | metal film resistor               | 20 Ω; 0.6 W             |                        |
| R5, R6               | metal film resistor               | 1 Ω; 0.6 W              |                        |
| T1, T2               | semi rigid coax                   | 50 Ω; 58 mm             | EZ-141-AL-TP-M17       |

<sup>[1]</sup> American Technical Ceramics type 100B or capacitor of same quality.

**Power LDMOS transistor** 

# 9. Package outline

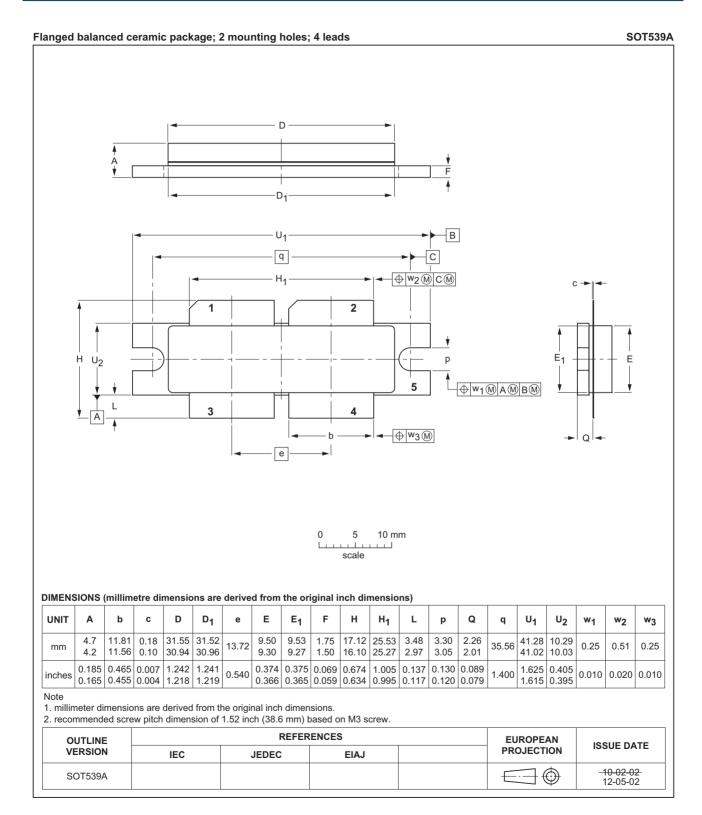


Fig 13. Package outline SOT539A

**Power LDMOS transistor** 

# 10. Handling information

#### CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

Table 10. ESD sensitivity

| ESD model                                                            | Class |
|----------------------------------------------------------------------|-------|
| Human Body Model (HBM); According to ANSI/ESDA/JEDEC standard JS-001 | 2 [1] |

<sup>[1]</sup> HBM classification 2 is granted to any part that passes after exposure to an ESD pulse of 2000 V, but fails after exposure to an ESD pulse of 4000 V.

### 11. Abbreviations

Table 11. Abbreviations

| Acronym | Description                                             |  |  |
|---------|---------------------------------------------------------|--|--|
| CW      | Continuous Wave                                         |  |  |
| EDGE    | Enhanced Data rates for GSM Evolution                   |  |  |
| GSM     | Global System for Mobile communications                 |  |  |
| HF      | High Frequency                                          |  |  |
| LDMOS   | Laterally Diffused Metal-Oxide Semiconductor            |  |  |
| LDMOST  | Laterally Diffused Metal-Oxide Semiconductor Transistor |  |  |
| RF      | Radio Frequency                                         |  |  |
| TTF     | Time To Failure                                         |  |  |
| VSWR    | Voltage Standing-Wave Ratio                             |  |  |

# 12. Revision history

Table 12. Revision history

| Document ID    | Release date                                        | Data sheet status    | Change notice | Supersedes |
|----------------|-----------------------------------------------------|----------------------|---------------|------------|
| BLF578 v.4     | 20161201                                            | Product data sheet   | -             | BLF578_3   |
| Modifications: | Section 10 on page 11: updated Handling information |                      |               |            |
| BLF578_3       | 20150901                                            | Product data sheet   | -             | BLF578_2   |
| BLF578_2       | 20100204                                            | Product data sheet   | -             | BLF578_1   |
| BLF578_1       | 20081211                                            | Objective data sheet | -             | -          |

#### **Power LDMOS transistor**

# 13. Legal information

#### 13.1 Data sheet status

| Document status[1][2]          | Product status[3] | Definition                                                                            |
|--------------------------------|-------------------|---------------------------------------------------------------------------------------|
| Objective [short] data sheet   | Development       | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification     | This document contains data from the preliminary specification.                       |
| Product [short] data sheet     | Production        | This document contains the product specification.                                     |

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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#### **Power LDMOS transistor**

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